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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/002,178	12/31/1997	MARK T. BOHR	042390P4220	7527

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EXAMINER
GUERRERO, MARIA F

ART UNIT	PAPER NUMBER
2822	

DATE MAILED: 04/09/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	09/002,178	BOHR, MARK T.	
	Examiner	Art Unit	
	Maria Guerrero	2822	

-- The MAILING DATE of this communication appears on the cov r sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on *30 January 2003* .

2a)☐ This action is **FINAL**. 2b)☒ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *31-43 and 45-54* is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☒ Claim(s) *31-43 and 45-54* is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☐ The drawing(s) filed on _____ is/are: a)☐ accepted or b)☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

11)☐ The proposed drawing correction filed on _____ is: a)☐ approved b)☐ disapproved by the Examiner.

If approved, corrected drawings are required in reply to this Office action.

12)☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

13)☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☐ All b)☐ Some * c)☐ None of:

1.☐ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____ .

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

14)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).

a) ☐ The translation of the foreign language provisional application has been received.

15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

1) ☒ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____ .
4) ☐ Interview Summary (PTO-413) Paper No(s). _____ .
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: .

DETAILED ACTION

1. This Office Action is in response to the Request for continued examination filed January 30, 2003.

Claims 1-30, 44 are canceled.

Claims 31-43 and 45-54 are pending.

Continued Examination Under 37 CFR 1.114

2. A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on January 30, 2003 has been entered.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

> (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

3. Claims 31-35, 37-43 and 45-54 are rejected under 35 U.S.C. 103(a) as being unpatentable over Efland et al. (U.S. 6,025,275) and Byrne (U.S. 5,136,364) in view of Camilletti et al. (U.S. 5,693,565).

Regarding claims 31-43 and 45-54, Efland et al. teaches forming a dielectric layer 22 over a metal layer on a substrate, the metal layer including a bond pad and a metal member space apart from the bond pad by a gap (fig. 1A), the dielectric layer 22 may be composed of several layers of dielectric having different makeup, the dielectric layer 22 may be composed by several layers (oxide, nitride, or polyimides) (col. 3, lines 40-45, col. 5, lines 25-30).

Efland et al. also discloses forming an opening (fig. 1A). Efland et al. teaches forming a conducting barrier layer 30 over the dielectric layer, over sidewalls of the opening, and over the exposed top surface of the bond pad (fig. 1B, the formation of a continuous seal is inhered). Furthermore, Efland et al. shows an electroplating process to form a copper lead 50 (fig. 1C, col. 5, lines 30-40).

Efland et al. does not specifically show the formation of first, second, and third material. However, Efland et al. teaches the dielectric layer 22 may be composed by several layers (oxide, nitride, or polyimides) (col. 3, lines 40-45, col. 5, lines 25-30). In addition, Byrne '364 shows the formation of the material to prevent moisture penetration (col. 2, lines 45-65).

Efland et al. fails to show forming the fourth material comprising an upper 4,000 Angstroms thick nickel vanadium film. However, this is known in the art as evidenced Byrne '364.

Byrne '364 discloses forming: a substrate 10, a bonding pad 11, a two component passivation layer, a first dielectric layer (silicon dioxide), a second dielectric layer (silicon nitride), a third dielectric layer can be a polyimide layer (fig. 3-5, col. 2,

lines 60-65, col. 3, lines 1-35). Byrne '364 also teaches forming an opening to exposed the top surface of the bonding pad, depositing a barrier layer (fig. 3). Byrne '364 discloses typically bumps are connected to the bonds pads. Byrne '364 also discloses a barrier layer comprising a nickel-vanadium layer (col. 2, lines 40-43). Furthermore, Byrne '364 discloses the formation of the bump as well known in the art (col. 1, lines 10-25).

Efland et al. and Byrne '364 fails to show the second material being kept out of the gap. However, Camilletti et al. teaches forming the second material being kept out of the gap (Fig. 2-4, col. 2, lines 45-55, col. 3, lines 45-67, col. 4, lines 10-17).

Therefore, it would have been obvious to a person of ordinary skill in the art at the time of the invention to modify the combination of Efland et al. and Byrne by including Camilletti et al. teaching. The modification would provide an interconnection that would exclude contaminants from the critical parts and would have a protection to avoid damage during the connection or test (Byrne, col. 1, lines 48-51; Camilletti et al., Abstract).

Allowable Subject Matter

4. Claim 36 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: the cited references fail to show or suggest the first material which completely

fill the gap between the bond pad and the first member being doped with fluorine atoms to reduce the dielectric constant.

Response to Arguments

5. Applicant's arguments with respect to claims 31-35, 37-43 and 45-54 have been considered but are moot in view of the new ground(s) of rejection.

6. Applicant argued that oxide does not have a low dielectric constant. However, silicon oxide has a dielectric constant of 4 or less and it is considered a low dielectric constant material compared to silicon nitride.

Conclusion

7. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Isobe (U.S. 5,677,239), Hsu et al. (U.S. 5,661,082), and Reche (U.S. 5,023,205) teach forming a first material over the metal layer having a thickness sufficient to completely fill a gap. Bohr (U.S. 6,143,638) (same Applicant) teaches forming a passivation structure.

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Maria Guerrero whose telephone number is 703-305-0162.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 703-308-49055. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

María Guerrero.

Maria Guerrero
Patent examiner
April 2, 2003